

MICROWAVE POWER GaAs FET

TIM1314-30L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 45.0dBm at 13.75GHz to 14.5GHz

·HIGH GAIN

G1dB= 5.0dB at 13.75GHz to 14.5GHz

LOW INTERMODULATION DISTORTION

IM3= -25dBc(Min.) at Pout= 38dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 7.0A f= 13.75 to 14.5GHz Two-Tone Test Po= 38dBm, Δf= 5MHz (Single Carrier Level)	dBm	44.0	45.0	
Power Gain at 1dB Gain Compression Point	G1dB		dB	4.0	5.0	
Drain Current	IDS1		Α		10.0	11.0
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%		22	_
3rd Order Intermodulation Distortion	IM3		dBc	-25		
Drain Current	IDS2		Α	_	9.0	10.1
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C			100

Recommended Gate Resistance (Rg): 10 Ω

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 9.6A	S	_	5.5	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 290mA	V	-0.7	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	20.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -290μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	1.0	1.1

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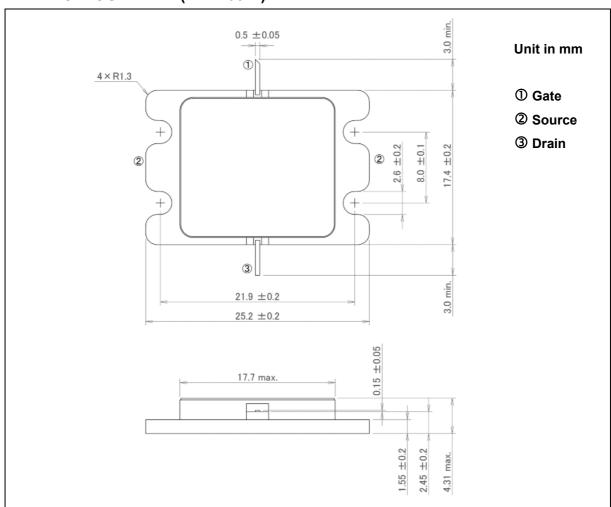
- MICROWAVE SEMICONDUCTOR TECHNICAL DATA



ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20
Total Power Dissipation (Tc= 25°C)	PT	W	136
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA03B)



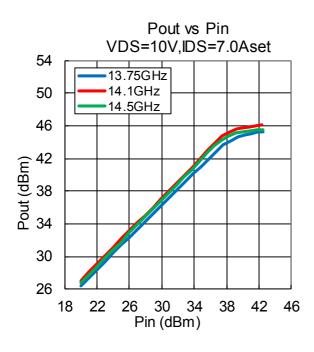
HANDLING PRECAUTIONS FOR PACKAGE MODEL

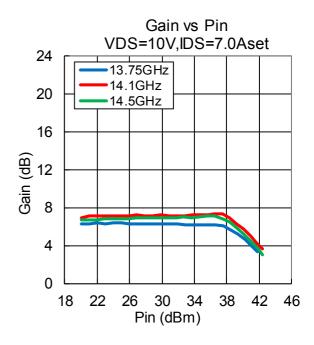
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C

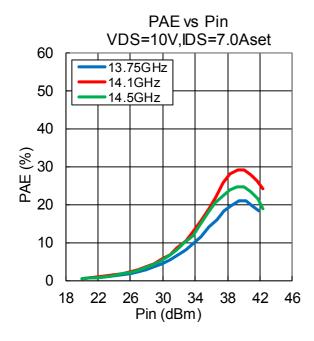
TYPICAL RF PERFORMANCE

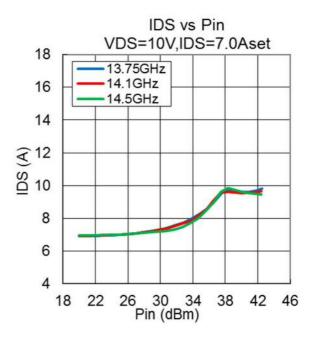
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 7.0 A, f= 13.75, 14.1, 14.5 GHz, Ta= +25 °C





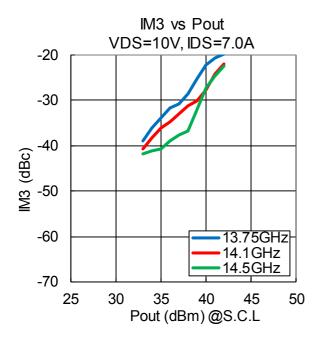


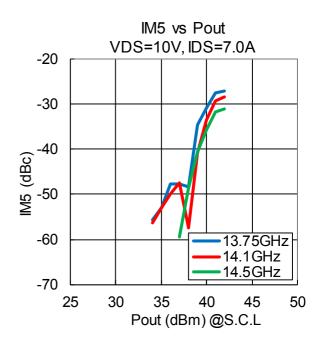




·IM3, IM5 vs. Pout

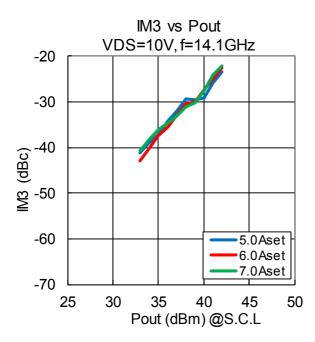
VDS= 10 V, IDSset= 7.0 A, f= 13.75, 14.1, 14.5 GHz, Δ f= 5 MHz , Ta= +25 °C

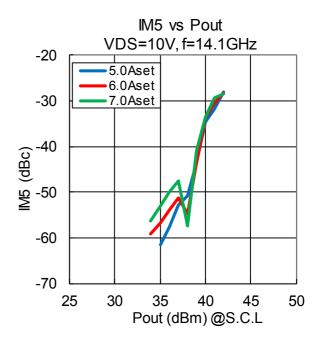




·IM3, IM5 vs. IDSset

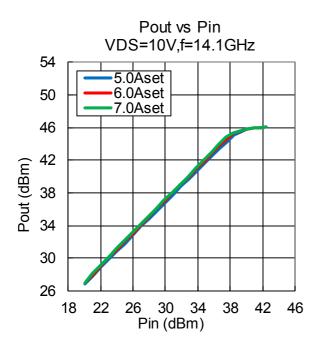
VDS= 10 V. IDSset= 5.0. 6.0. 7.0 A. f= 14.1 GHz. Δ f= 5 MHz . Ta= +25 °C

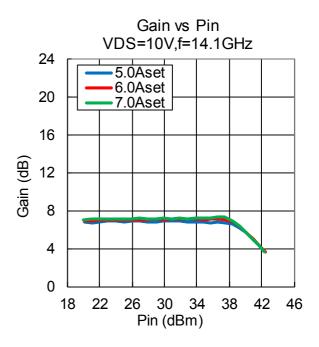


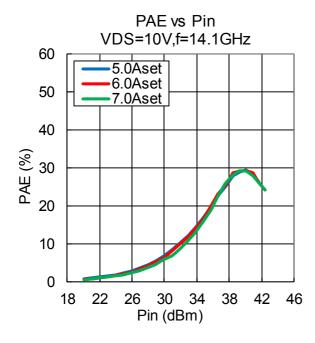


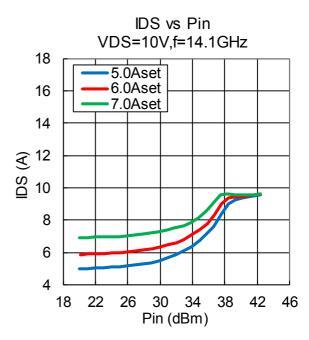
·Pout, Gain, PAE, IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 5.0, 6.0, 7.0 A, f= 14.1 GHz, Ta= +25 °C





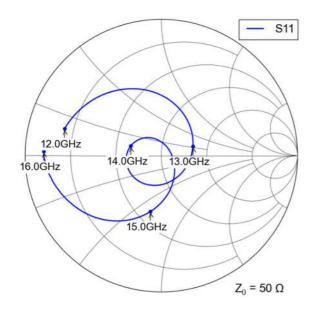


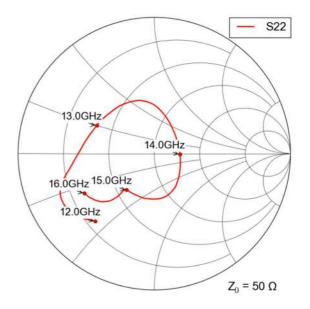


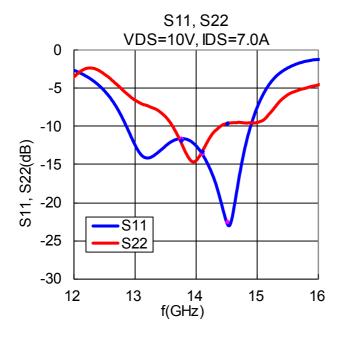


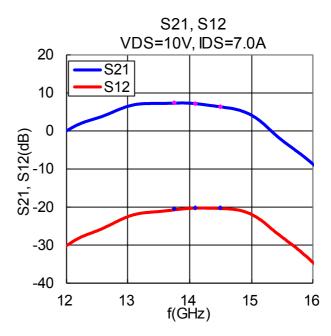
·S-Parameters

VDS= 10 V, IDSset= 7.0 A, f= 12.0 to 16.0 GHz, Ta= +25 °C











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